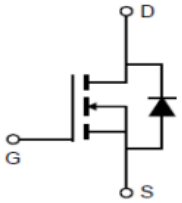
General Description:

The LWT4T02HD5 uses advanced SGT technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is PDFN5*6-8L, which accords with the ROHS standard and Halogen Free standard.

V_{DSS}	40	V
I_D	150	A
P_D	89	W
$R_{DS(ON)\ TYPE}$	1.4	mΩ

Marking and Pin Assignment

Inner Equivalent Principium Chart



Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

Applications:

- DC-DC Converter
- Portable Equipment
- Power Management

100% DVDS Tested

100% Avalanche Tested

Package Marking and Ordering Information:

Marking	Part Number	Package	Packing	Qty.
T4T02H/LW D5/D.C.	LWT4T02HD5	PDFN5*6-8L	Reel	5000 Pcs

Absolute Maximum Ratings:

Symbol	Parameter		Value	Units
V_{DSS}	Drain-to-Source Voltage		40	V
I_D	Continuous Drain Current	T_C=25℃	150	A
	Continuous Drain Current	T_C=100℃	95	A
I_{DM}[a1]	Pulsed Drain Current		600	A
E_{AS}[a2]	Single pulse avalanche energy		242	mJ
V_{GS}	Gate-to-Source Voltage		±20	V
P_D	Power Dissipation		89	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		150, -55 to 150	℃
T_L	Maximum Temperature for Soldering		260	℃

Thermal Characteristics:

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.4	℃/W
$R_{\theta JA}$[a3]	Thermal Resistance, Junction-to-Ambient	40	℃/W

Electrical Characteristic (T_J = 25 °C, unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	40	--	--	V
I_{DSS}	Drain to Source Leakage Current	V_{DS}=40V, V_{GS}=0V	--	--	1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	V_{GS}=+20V, V_{DS}=0V	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	V_{GS}=-20V, V_{DS}=0V	--	--	-100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	2.2	2.6	3.0	V
$R_{DS(ON)}$	Drain-to-Source On-Resistance	V_{GS}=10V, I_D=20A	--	1.4	2.0	mΩ

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	V_{GS} =0V V_{DS} =20V f = 1.0MHz	--	3579	--	pF
C_{oss}	Output Capacitance		--	1828	--	
C_{rss}	Reverse Transfer Capacitance		--	87.8	--	
R_G	Gate resistance	V_{GS}=0V,V_{DS}=0V,f=1MHz	--	2.5	--	Ω

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	I_D =20A V_{DS} =20V V_{GS} =10V R_G =3.0Ω	--	13.8	--	ns
t_r	Rise Time		--	33.4	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	46	--	
t_f	Fall Time		--	24.4	--	
Q_g	Total Gate Charge	V_{GS} =10V V_{DS} =20V I_D =20A	--	52	--	nC
Q_{gs}	Gate to Source Charge		--	12.5	--	
Q_{gd}	Gate to Drain Charge		--	8.2	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	T_C =25 °C	--	--	150	A
V_{SD}	Diode Forward Voltage	I_S=20A, V_{GS}=0V	--	--	1.2	V
t_{rr}	Reverse Recovery time	I_S=20A, V_{DD}=20V dI/dt=100A/μs	--	37	--	ns
Q_{rr}	Reverse Recovery Charge		--	20.2	--	nC

a1：Repetitive rating; pulse width limited by maximum junction temperature

a2：V_{DD}=25V, L=0.1mH, R_G=25Ω, Starting TJ=25 ℃

a3：Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 μm thick) copper area for drain connection.

Characteristics Curve：

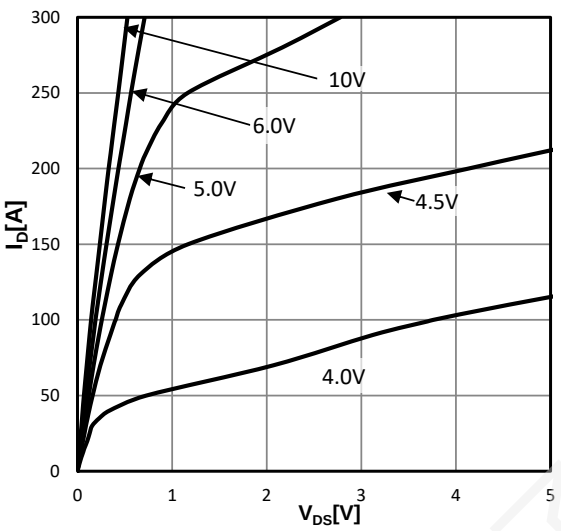
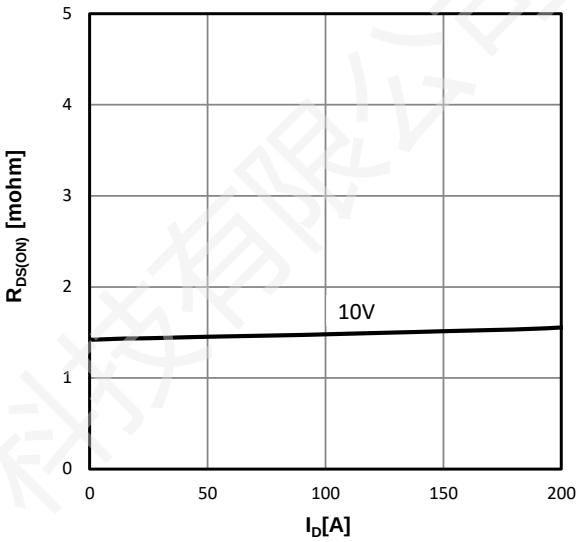
Figure 1: Typ. output characteristics	Figure 2: Typ. drain-source on resistance
	
$I_D=f(V_{DS})$, T_j=25 °C; parameter: V_{GS}	$R_{DS(on)}=f(I_D)$, T_j=25 °C; parameter: V_{GS}

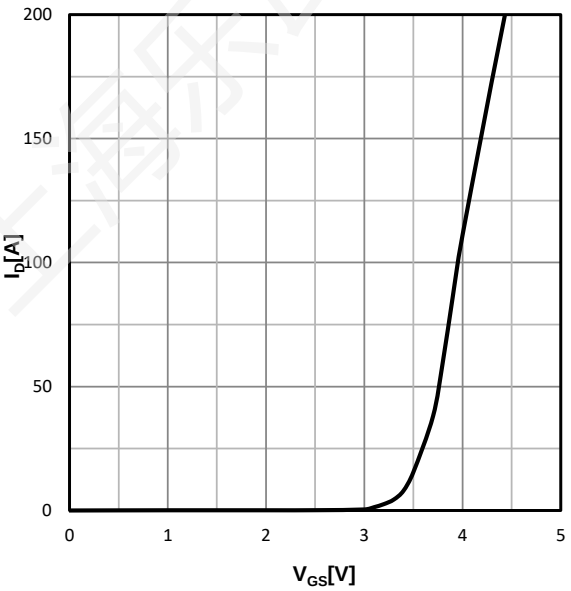
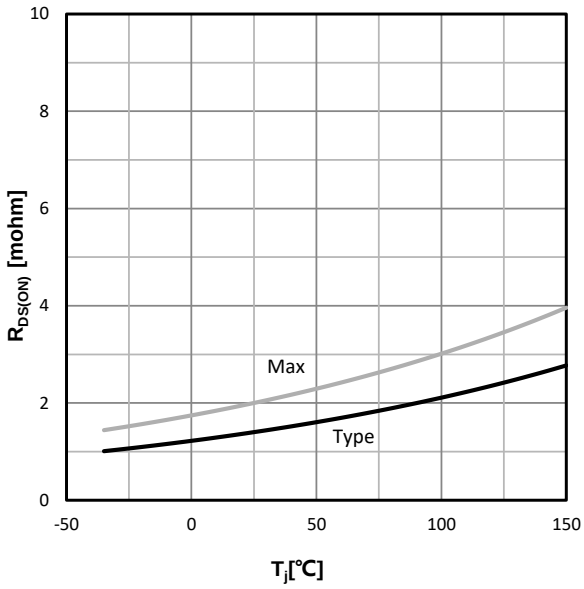
Figure 3: Typ. transfer characteristics	Figure 4: drain-source on resistance
	
$I_D=f(V_{GS})$, $\|V_{DS}\|>2\|I_D\|R_{DS}(on)max$;	$R_{DS(on)}=f(T_j)$, I_D=20A, V_{GS}=10V;

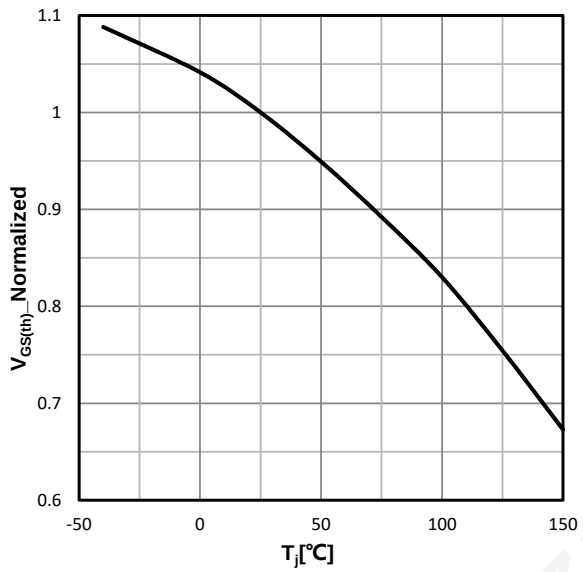
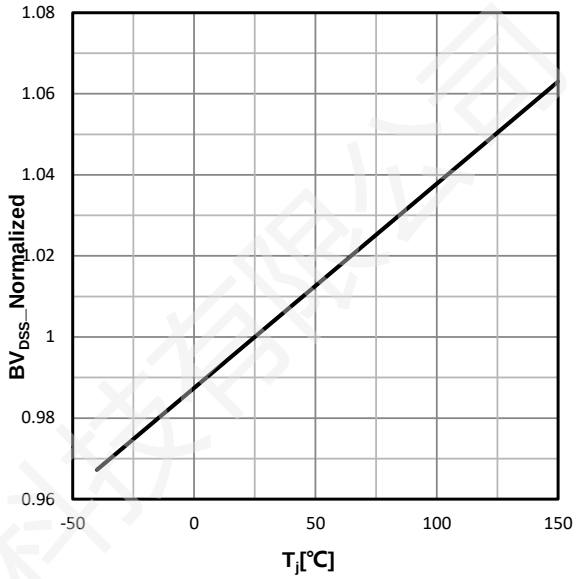
Figure 5: Typ. gate threshold voltage	Figure 6: Drain-source breakdown voltage
	
V_{GS}=f(T_j),I V_{GS}=$V_{DS,}$$I_D$=250μA;	$V_{BR(DSS)}$=f(T_j); I_D=250μA;

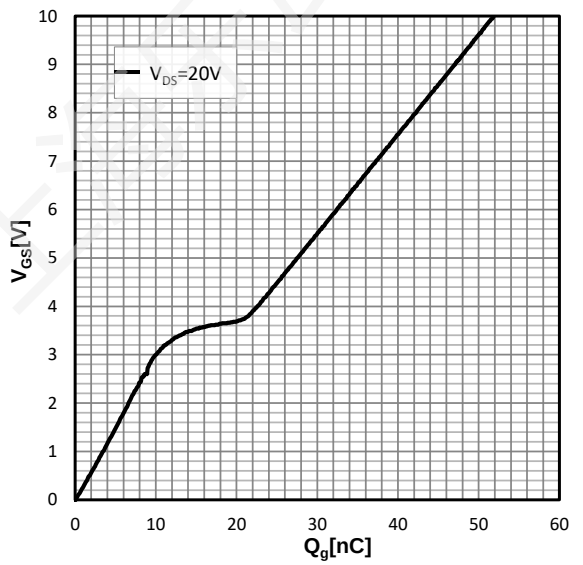
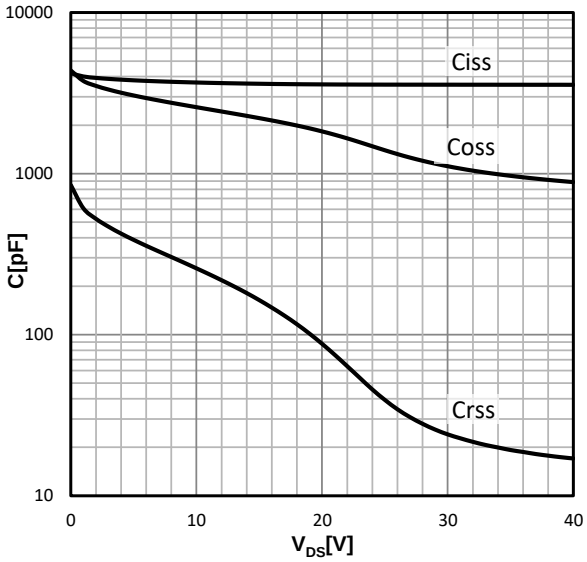
Figure 7: Typ. gate charge	Figure 8: Typ. Capacitances
	
V_{GS}=f(Q_g), I_D=20A, T_j=25 °C; parameter: V_{DS}	C=f(V_{DS}); V_{GS}=0V; f=1.0 MHz;

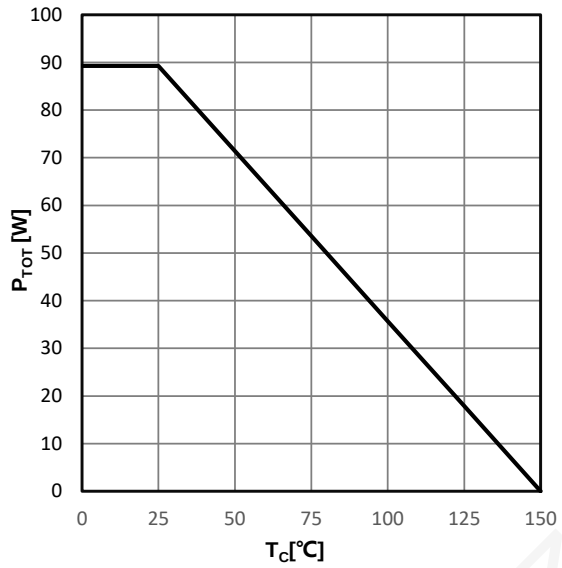
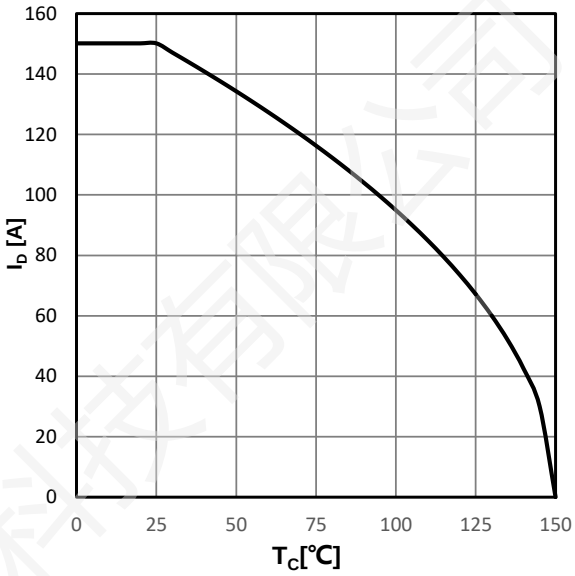
Figure 9: Power dissipation	Figure 10:Drain current
	
$P_{tot}=f(T_C)$;	$I_D=f(T_C)$;

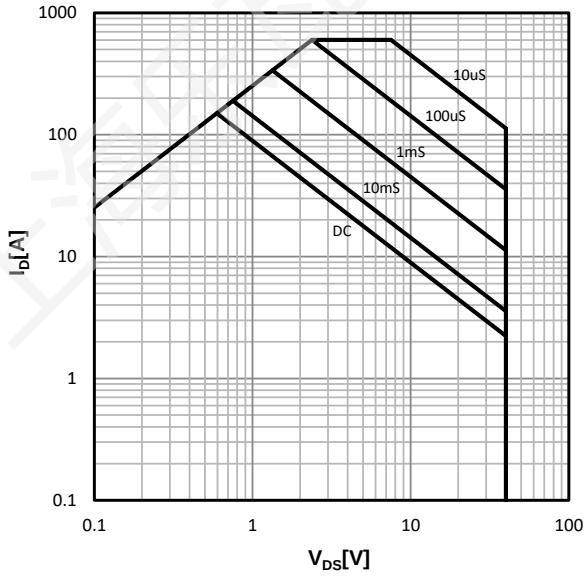
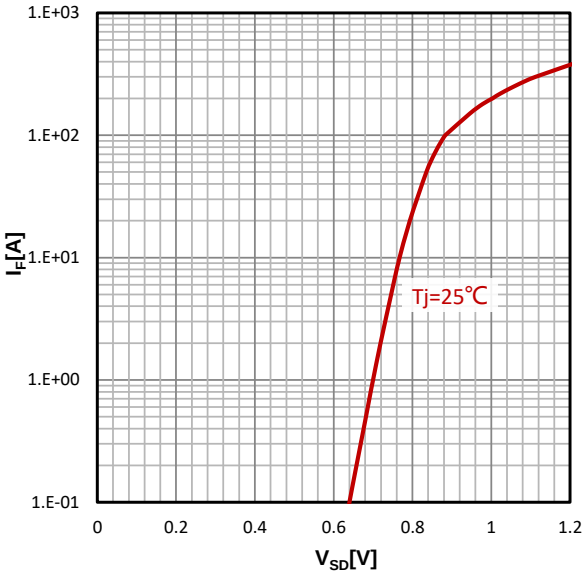
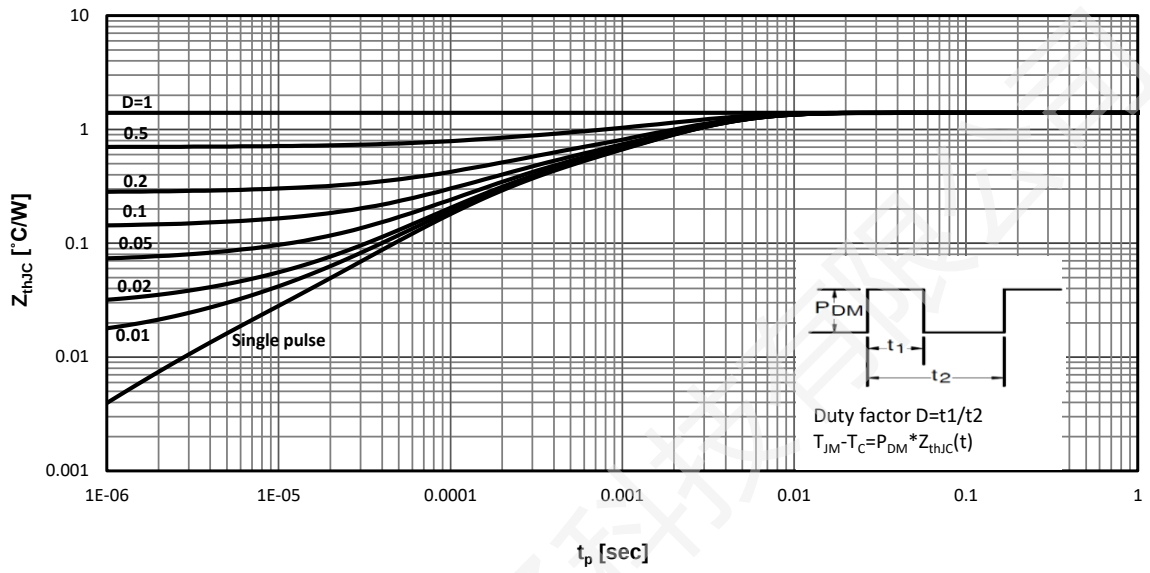
Figure 11: Safe operating area	Figure 12: Typ. forward characteristics
	
$I_D=f(V_{DS})$; T_C=25 °C; D=0; parameter: tp	$I_F=f(V_{SD})$;

Figure 13: Max. Transient Thermal Impedance



$Z_{thJC}=f(t_p)$; parameter: D

Test Circuit & Waveform:

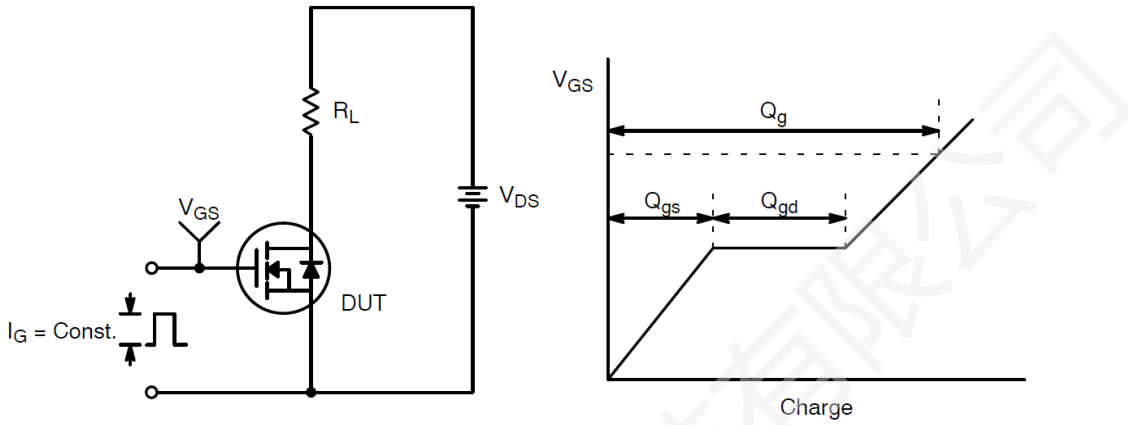


Figure 14: Gate Charge Test Circuit & Waveform

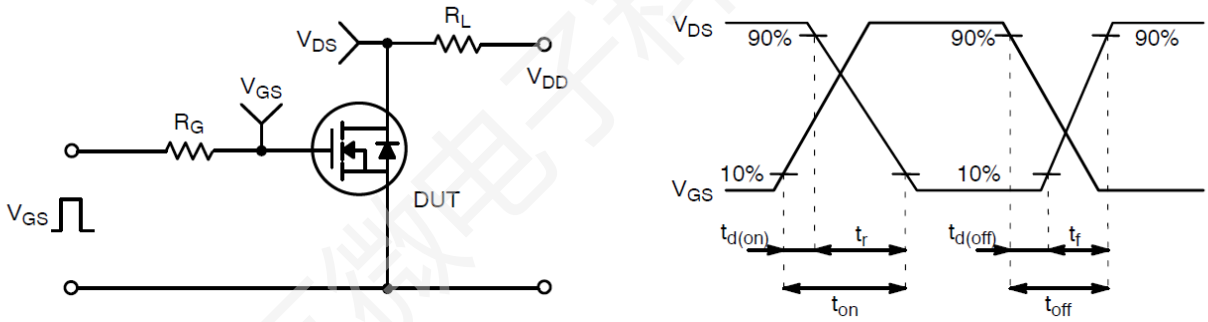


Figure 15: Resistive Switching Test Circuit & Waveforms

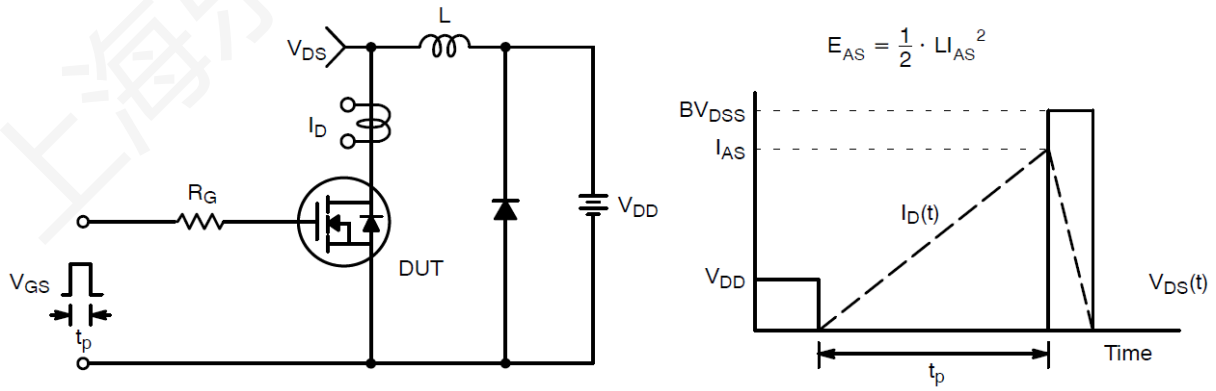
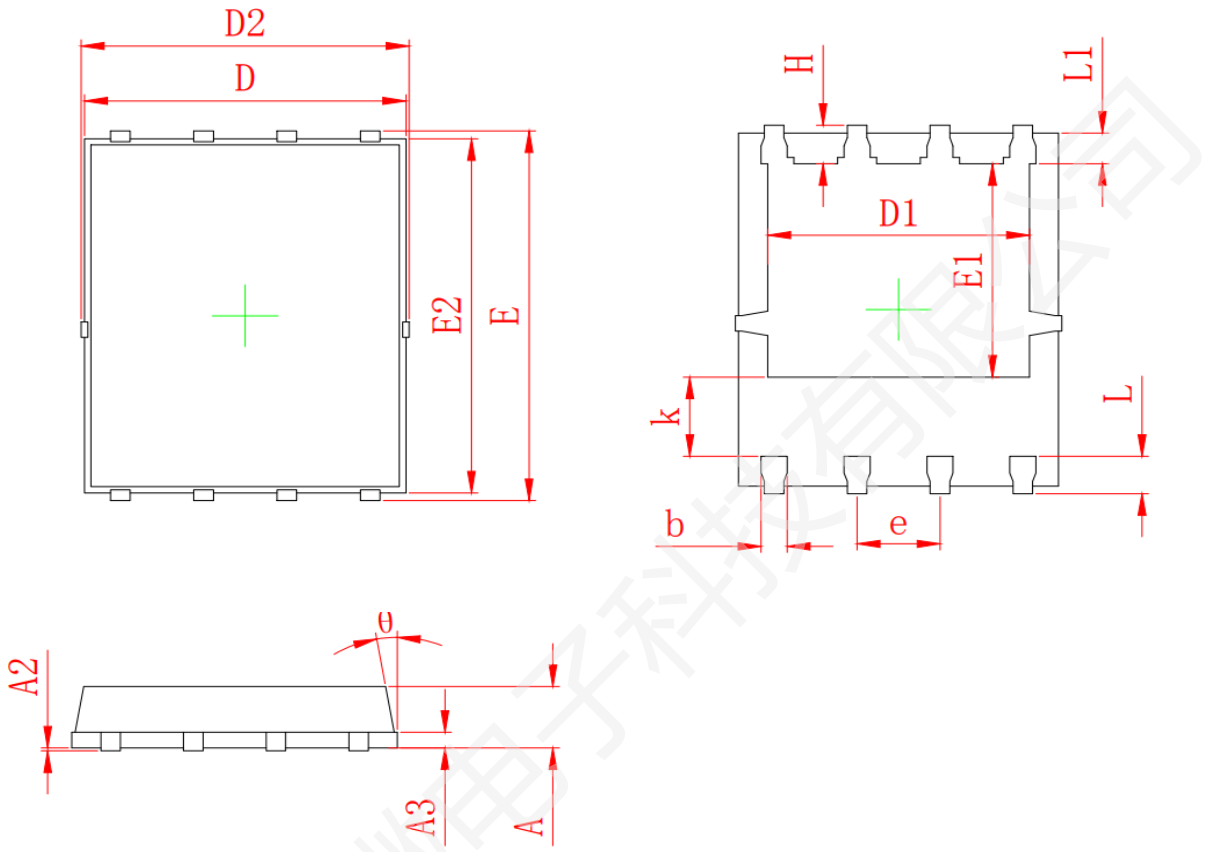


Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline:



Symbol	MILLIMETER	
	Min	Max
A	0.900	1.200
A1	0.254 REF	
A2	0~0.050	
D	4.824	4.976
D1	3.910	4.110
D2	4.944	5.076
E	5.924	6.076
E1	3.375	3.575
E2	5.674	5.826
b	0.350	0.450
e	1.270 TYP	
L	0.534	0.686
L1	0.424	0.576
k	1.190	1.390
H	0.549	0.701
θ	8°	12°

Revision History:

Revison	Date	Descriptions
Rev 1.1	Feb.2025	Initial Version

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